

ABSTRACT

There is provided a method of producing a bonded wafer comprising bonding a bond wafer and a base wafer via an oxide film or directly and then reducing thickness of the bond wafer, characterized in that the base wafer is a wafer produced by processes comprising slicing a silicon single crystal ingot, and then subjected at least to chamfering, lapping, etching, mirror polishing and cleaning, and the etching process is conducted by subjecting the wafer to alkali etching, and then acid etching, and an etching amount in the alkali etching is larger than an etching amount in the acid etching, and a chamfered part of the base wafer is subjected to a mirror finishing process after the etching, and a bonded wafer produced by the method. There can be provided a base wafers for a bonded wafer having good flatness wherein generation of particles from a chamfered part or a back surface is reduced in high productivity, and a bonded wafer wherein very few particles are generated, having SOI layer or silicon active layer excellent in flatness and thickness uniformity and a method of producing it.